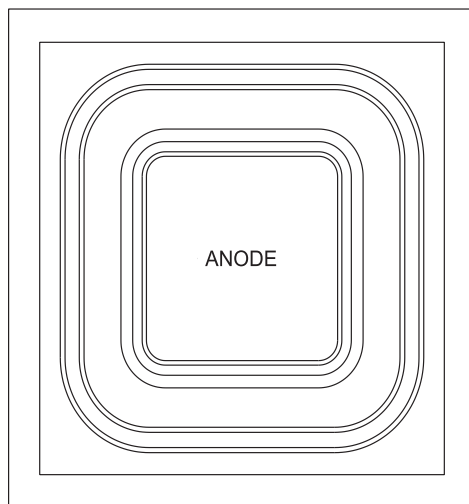


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au.As - 13,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

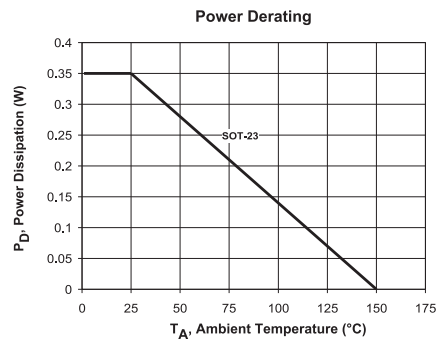
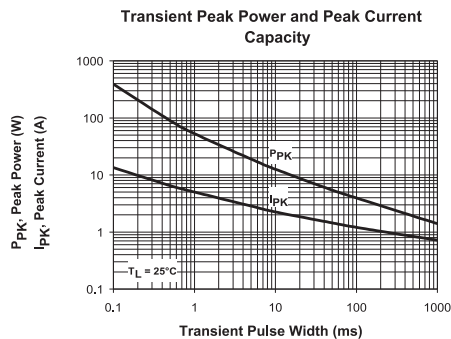
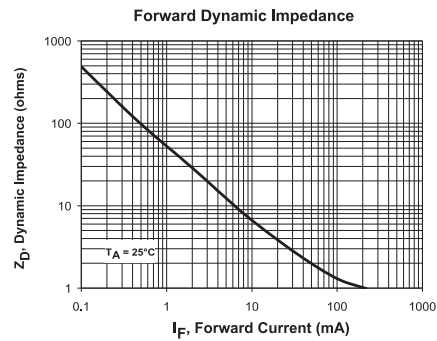
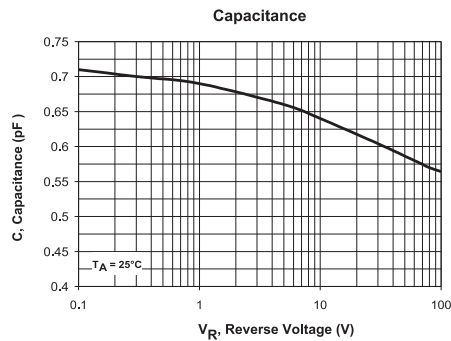
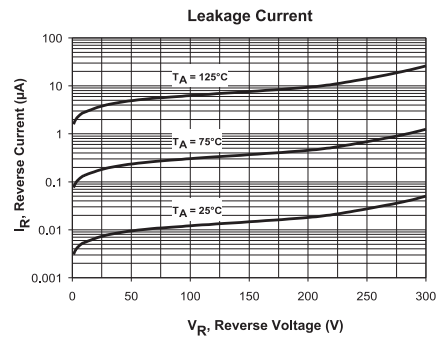
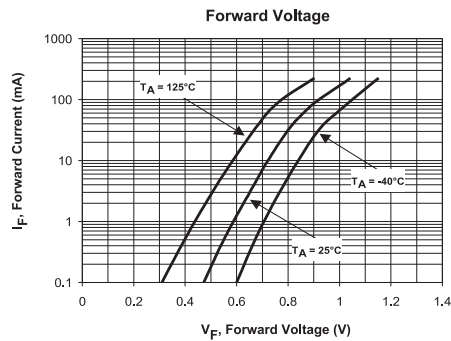
45,050

PRINCIPAL DEVICE TYPES

CMPD2003
CMPD2004
CMPD2005
1N3070
CMDD2004
CMSD2004
CMOD2004
CMXD2004
CMLD2004

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R0 (17-August 2004)



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